RF POWER FET
N-Channel Enhancement Mode

DESCRIPTION:

The **ASI MRF173** is Designed for wideband large-signal output and driver stages up to 200 MHz frequency range.

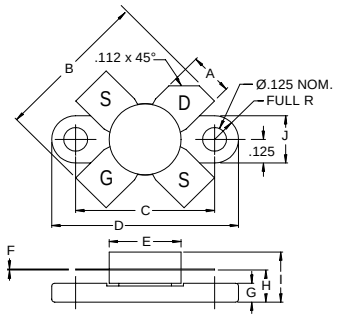
FEATURES:

- P_G = 11 dB Min. at 150 MHz
- **30:1 Load VSWR** Capability
- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

I_D	9.0 A
V_{DSS}	65 V
V_{GS}	±40 V
P_{DISS}	220 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	0.8 °C/W

PACKAGE STYLE .500 4L FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.785 / 19.94	
C	.720 / 18.29	.730 / 18.54
D	.970 / 24.64	.980 / 24.89
E		.385 / 9.78
F	.004 / 0.10	.006 / 0.15
G	.085 / 2.16	.105 / 2.67
H	.160 / 4.06	.180 / 4.57
I		.280 / 7.11
J	.240 / 6.10	.255 / 6.48

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{DSS}	I_{DS} = 50 mA			65			V
I_{DSS}	V_{DS} = 28 V	V_{GS} = 0 V				2.0	mA
I_{GSS}	V_{DS} = 0 V	V_{GS} = 40 V				1.0	µA
$V_{GS(th)}$	I_D = 50 mA	V_{DS} = 10 V		1.0		6.0	V
g_{fs}	I_D = 2.0 A	V_{DS} = 10 V		1.8	2.2		mho
C_{iss} C_{oss} C_{rss}	V_{DS} = 28 V	V_{GS} = 0 V	f = 1.0 MHz		110 105 10		pF
P_G	V_{DD} = 28 V	I_{DQ} = 50 mA	P_{out} = 80 W	11	13		dB
η_D			f = 150 MHz	55	60		%
ψ	V_{SWR} = 30:1 AT ALL PHASE ANGLES			NO DEGRADATION IN OUTPUT POWER			